

## **AMENDMENTS TO THE CLAIMS**

This listing of claims will replace all prior versions and listings of claims in this application. As compared to the prior versions and listings of the claims, Claims 1 and 7 have been amended.

### **Listing of Claims:**

1. (Currently Amended) A semiconductor structure comprising:
  - a first semiconductor region characterized by a dopant concentration greater than  $1 \times 10^{19}/\text{cm}^3$ ;
  - a second semiconductor region overlying the first semiconductor region, said second semiconductor region comprising silicon and characterized by a dopant concentration less than  $1 \times 10^{18}/\text{cm}^3$  and a thickness  $t_1$ ; and
  - a layer comprising titanium directly overlying the second semiconductor region, said layer characterized by a line width no greater than  $0.3\mu\text{m}$  and a thickness  $t_2$ , wherein  $t_1 > 1.2t_2$ ;

$t_1/t_2$  being sufficiently small that, when the layer is reacted with the second semiconductor region to form titanium disilicide, the titanium disilicide is in ohmic contact with the first semiconductor region;

$t_1/t_2$  being sufficiently large that, when the layer is reacted with the second semiconductor region to form titanium disilicide, the titanium disilicide anneals to a phase with a sheet resistance less than 3 ohms/square.
2. (Previously Presented) The semiconductor structure of Claim 1 wherein  $t_1 \geq 2.2t_2$ .

3. (Previously Presented) The semiconductor structure of Claim 1 wherein  $t_1 = 2.3t_2, \pm 0.1t_2$ .
4. (Previously Presented) The semiconductor structure of Claim 1 wherein  $t_1$  is about  $600\text{\AA}$  and  $t_2$  is about  $250\text{\AA}$ .
5. (Previously Presented) The semiconductor structure of Claim 1 wherein the dopant concentration of the first semiconductor region is greater than  $1 \times 10^{20}/\text{cm}^3$ .
6. (Previously Presented) The semiconductor structure of Claim 1 or 5 wherein the first semiconductor region is doped primarily with boron.
7. (Currently Amended) A semiconductor structure comprising:  
a first semiconductor region characterized by a boron dopant concentration greater than  $1 \times 10^{20}/\text{cm}^3$ ; and  
a set of titanium silicide conductors directly overlying the first semiconductor region and in ohmic contact therewith, each said conductor characterized by a width no greater than  $0.3\mu\text{m}$ , and at least 90% of said conductors characterized by a sheet resistance less than 3 ohms/square;  
wherein the set of titanium silicide conductors is formed, in part, by a second semiconductor region overlying the first semiconductor region, said second semiconductor region comprising silicon and characterized by a dopant concentration less than  $1 \times 10^{18}/\text{cm}^3$ .

8. (Previously Presented) The semiconductor structure of Claim 1 or 7 wherein the semiconductor structure comprises a 3-D memory array, wherein the 3-D memory array comprises a plurality of memory cells arranged in a plurality of layers stacked vertically above one another in a single chip.